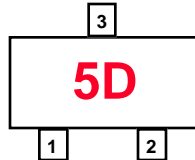
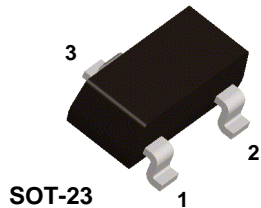
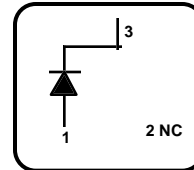


MMBD914



CONNECTION DIAGRAM



High Conductance Ultra Fast Diode

Sourced from Process 1P. See 1N4148 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W_{IV}	Working Inverse Voltage	75	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current	600	mA
i_f	Recurrent Peak Forward Current	700	mA
$i_{f(surge)}$	Peak Forward Surge Current		
	Pulse width = 1.0 second	1.0	A
	Pulse width = 1.0 microsecond	2.0	A
T_{stg}	Storage Temperature Range	-55 to +150	°C
T_J	Operating Junction Temperature	150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MMBD914*	
P_D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

* Device mounted on glass epoxy PCB 1.6" X 1.6" X 0.06"; mounting pad for the collector lead min. 0.93 in2

High Conductance Ultra Fast Diode

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
B _V	Breakdown Voltage	I _R = 100 μA I _R = 5.0 μA	100 75		V V
I _R	Reverse Current	V _R = 20 V V _R = 20 V, T _A = 150°C V _R = 75 V		25 50 5.0	nA μA μA
V _F	Forward Voltage	I _F = 10 mA		1.0	V
C _O	Diode Capacitance	V _R = 0, f = 1.0 MHz		4.0	pF
T _{RR}	Reverse Recovery Time	I _F = 10 mA, V _R = 6.0 V, I _{RR} = 1.0 mA, R _L = 100Ω		4.0	nS
V _{FM}	Peak Forward Recovery Voltage	I _F = 50 mA PEAK SQUARE WAVE PULSE WIDTH = 0.1 μS 5 kHz - 100 kHz REP RATE		2.5	v

MMBD914